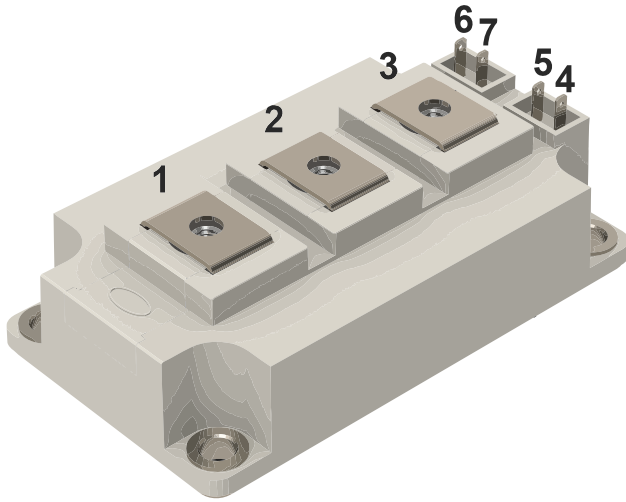


Industry standard 62mm IGBT module
1200V 200A

Chip features

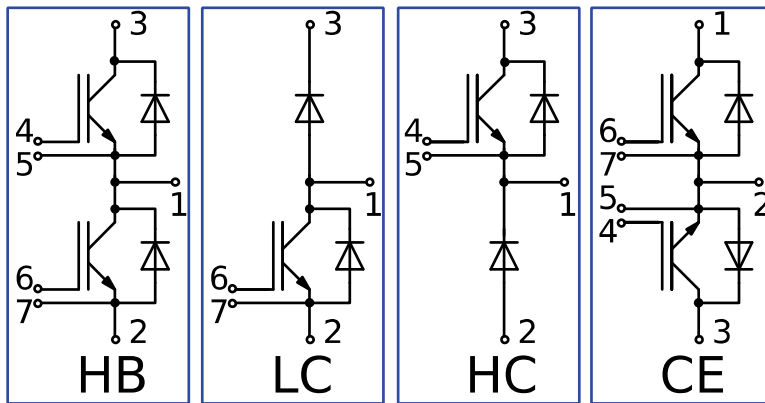
- IGBT Chip
 - low $V_{CE(sat)}$ value
 - 10 μ s short circuit @ 150°C
 - square RBSOA @ $2 \times I_c$
 - low EMI
- FRD Chip
 - fast and soft reverse recovery
 - low voltage drop

Design features

- copper baseplate
- Al₂O₃ DBC substrate
- ultrasonically welded power terminals
- improved thermal cycling
- RoHS compliant

Typical application

- AC motor drives
- solar inverter
- air conditioning
- high power converters and UPS


Maximum rated values

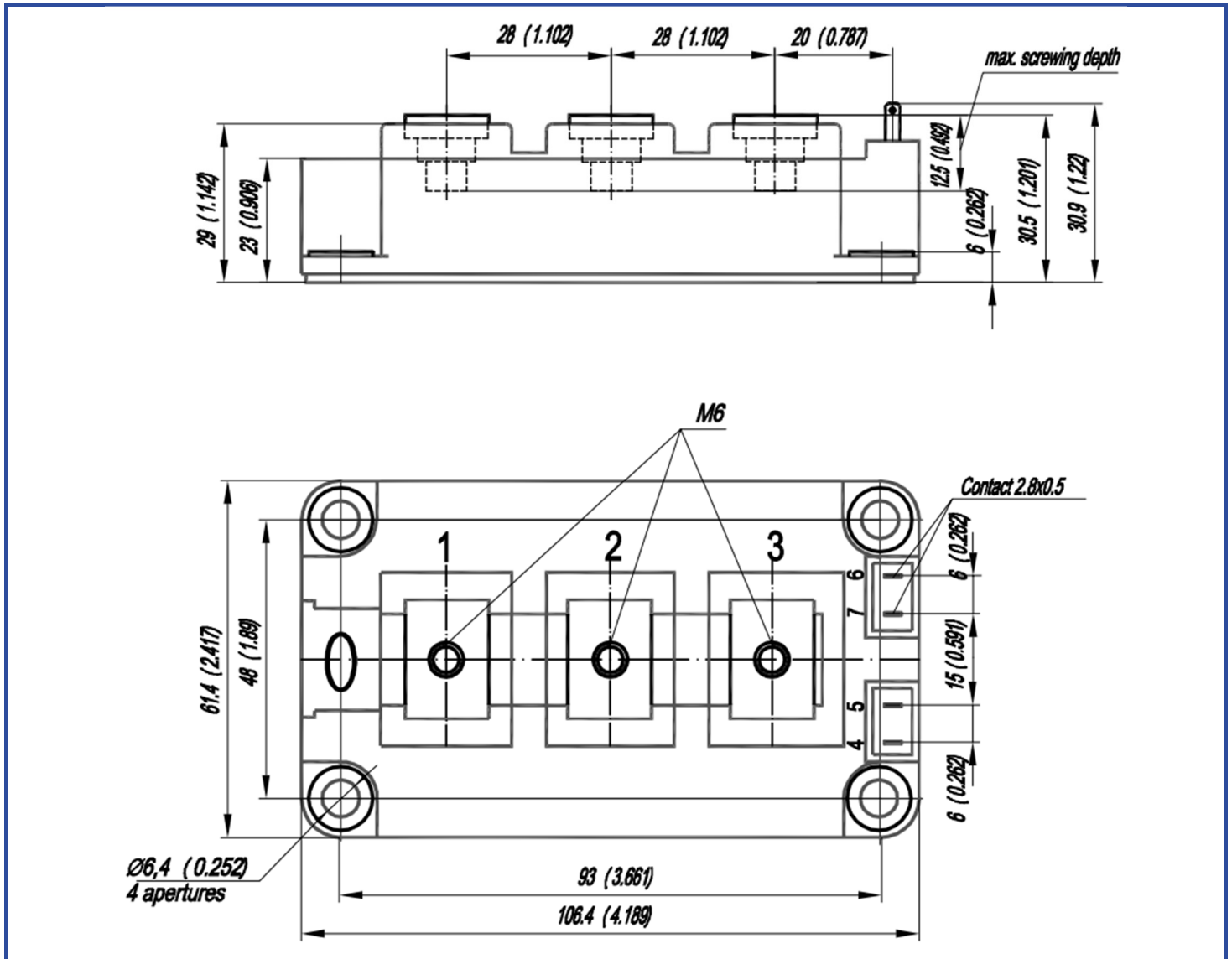
Definition	Symbol	Conditions	Value	Unit
IGBT				
Collector-Emitter voltage	V_{CES}	$V_{GE} = 0V$	1200	V
Collector current (nominal)	$I_{C\ nom}$		200	A
Collector current (maximum continuous)	$I_{C\ 25}$	$T_j = 175^\circ C, T_c = 25^\circ C$	311	A
	$I_{C\ 80}$	$T_j = 175^\circ C, T_c = 80^\circ C$	237	A
Repetitive peak collector current *1	I_{CRM}	$I_{CRM} = 3 \times I_{C\ nom}, t_p = 1ms$	600	A
Gate-Emitter voltage	V_{GES}		± 20	V
Junction temperature	T_j		-40 ... 175	°C
Inverse diode / Freewheeling diode				
Repetitive peak reverse voltage	V_{RRM}	$V_{GE} = 0V$	1200	V
Forward current (nominal)	$I_{F\ nom}$		200	A
Forward current (maximum continuous)	$I_{F\ 25}$	$T_j = 175^\circ C, T_c = 25^\circ C$	248	A
	$I_{F\ 80}$	$T_j = 175^\circ C, T_c = 80^\circ C$	181	A
Repetitive peak forward current *1	I_{FRM}	$I_{FRM} = 3 \times I_{F\ nom}, t_p = 1ms$	600	A
Surge (non-repetitive) forward current	I_{FSM}	$t_p = 1ms, \sin 180^\circ, T_j = 25^\circ C$	990	A
Junction temperature	T_j		-40 ... 175	°C
Module				
Storage temperature	T_{stg}		-40 ... 125	°C
Isolation voltage	V_{isol}	AC sinus 50 Hz, t = 1min	4000	V

*1 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed maximum T_j rating.



Characteristics

Definition	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
IGBT							
Collector-Emitter saturation voltage	V_{CEsat} (chip)	$V_{GE} = 15V$ $I_C = 200A$	$T_J = 25^\circ C$	-	1.75	2.2	V
			$T_J = 150^\circ C$	-	2.2	2.5	V
	V_{CEsat} (terminal)		$T_J = 25^\circ C$	-	1.85	2.3	V
			$T_J = 150^\circ C$	-	2.3		V
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C = 8mA, V_{CE} = V_{GE}, T_J = 25^\circ C$	5.5	6	6.5	V	
Collector-Emitter cut-off current	I_{CES}	$V_{CE} = 1200V$ $V_{GE} = 0V$	$T_J = 25^\circ C$	-	100	300	μA
			$T_J = 150^\circ C$	-	-	2000	μA
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	400	nA	
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V$ $f = 1MHz, T_J = 25^\circ C$	-	12	-	nF	
Output capacitance	C_{oes}		-	1180	-	pF	
Reverse transfer capacitance	C_{res}		-	1178	-	pF	
Total gate charge	Q_G	$I_C = 200A, V_{CE} = 600V, V_{GE} = -8 \div 20V$	-	2210	-	nC	
Internal gate resistance	R_{Gint}	$T_J = 25^\circ C$	-	3.8	-	Ω	
Turn-on delay time	$t_{d(on)}$	$V_{CE} = 600V, I_C = 200A,$ $R_G = 3.0\Omega, V_{GE} = \pm 15V,$ $T_J = 150^\circ C,$ $di/dt_{on} = 7000 A/\mu S,$ $di/dt_{off} = 2300 A/\mu S,$ $du/dt_{off} = 6900 V/\mu S$	-	320	384.0	ns	
Rise time	t_r		-	45	54.0	ns	
Turn-on energy	E_{on}		-	14	16.8	mJ	
Turn-off delay time	$t_{d(off)}$		-	550	660.0	ns	
Fall time	t_f		-	72	86.4	ns	
Turn-off energy	E_{off}		-	22	26.4	mJ	
Short circuit duration	t_{psc}	$V_{CC} = 720V, V_{GE} \leq 20V,$ $T_J = 150^\circ C, \text{non-repetitive}$	-	-	10	μs	
Collector-emitter threshold voltage	V_{CE0}	$V_{GE} = 15V, T_J = 150^\circ C$	-	0.88	0.98	V	
On-State slope resistance (IGBT)	r_{CE0}	for static power loss calculation	-	6.6	7.6	m Ω	
Thermal resistance junction to case	$R_{th(j-c)}$	per IGBT	-	-	0.14	K/W	
Inverse diode / Freewheeling diode							
Continuous forward voltage	V_F (chip)	$I_F = 200A$	$T_J = 25^\circ C$	-	1.9	2.2	V
			$T_J = 150^\circ C$	-	1.9	-	V
	V_F (terminal)		$T_J = 25^\circ C$	-	2.0	2.3	V
			$T_J = 150^\circ C$	-	2.0	-	V
Reverse recovery time	t_{rr}	$V_R = 600V$ $I_F = 200A$ $di_F/dt = 3200$ μS	$T_J = 25^\circ C$	-	200	240.0	ns
Peak reverse recovery current	I_{RM}		$T_J = 125^\circ C$	-	350	420.0	ns
			$T_J = 25^\circ C$	-	150	180.0	A
Reverse recovered charge	Q_{rr}		$T_J = 125^\circ C$	-	200	240.0	A
			$T_J = 25^\circ C$	-	12	14.4	μC
Reverse recovery energy	E_{rr}		$T_J = 125^\circ C$	-	25	30.0	μC
		$T_J = 25^\circ C$	-	3.6	240.0	mJ	
		$T_J = 125^\circ C$	-	8	420.0	mJ	
Forward threshold voltage (Diode)	V_{F0}	$T_J = 175^\circ C$	-	1.2	-	V	
On-state slope resistance (Diode)	r_F	for static power loss calculation	-	4.5	-	m Ω	
Thermal resistance junction to case	$R_{th(j-c)}$		-	-	0.26	K/W	
Module							
Parasitic inductance Collector-Emitter	L_{CE}		-	30	-	nH	
Resistance terminal-chip	$R_{CC'+REE'}$	terminal-chip $T_J = 25^\circ C$	-	0.5	-	m Ω	
Thermal resistance case to heatsink	R_{thCH}	per module	-	0.05	-	K/W	
Mounting torque for screws to heatsink	M_s	to heatsink M6	3	-	5	Nm	
Mounting torque for terminal screws	M_t	to terminals M5	2.5	-	5	Nm	
Weight	W		-	-	340	g	

Overall dimensions: Package type AA

Part numbering guide

MIAA	-	HB	12	FA	-	200	N	
MIAA								IGBT module package type: AA
		HB						2 switches as Half-Bridge
		HC						1 switch as High-Side chopper
		LC						1 switch as Low-Side chopper
		CE						2 switches with Common Emitter
			12					Voltage rating ($V_{CES}/100$)
				FA				IGBT+FRD chipset modification
						200		Current Rating
							N	Climatic version: normal climate

This datasheet is a tentative target data. The information in this document will be updated according to product qualification test results.

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